NSN 5961-01-021-4899

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View Online at https://aerobasegroup.com/nsn/5961-01-021-4899 **Inclosure Material:** Metal **Overall Length:** 0.720 inches **Overall Diameter:** 1.250 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Thread Size:** 0.375 inches **Semiconductor Material:** Germanium Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-base, emitter open and 60.0 breakdown voltage, collector-to-emitter, base open and 30.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 10.00 amperes source cutoff current and 65.00 amperes source cutoff current **Power Rating Per Characteristic:** 66.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius case **Special Features:** Junction pattern arrangement: pnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 pin **Specification Data:** 80131-release4186 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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